
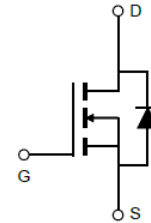
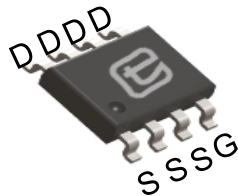


**60V N-Channel SGT MOSFET**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>● Trench Power SGT technology</li> <li>● Very low on-resistance <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Excellent Gate Charge x <math>R_{DS(ON)}</math> Product</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>● High Frequency Switching and Synchronous Rectification</li> </ul>	<p><b>Product Summary</b></p> <table> <tr> <td><math>V_{DS}</math></td> <td>60V</td> </tr> <tr> <td><math>I_D</math> (at <math>V_{GS}=10V</math>)</td> <td>13A</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>)</td> <td>&lt; 9m<math>\Omega</math></td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>)</td> <td>&lt; 13.5m<math>\Omega</math></td> </tr> </table> <p>100% UIS Tested</p> 	$V_{DS}$	60V	$I_D$ (at $V_{GS}=10V$ )	13A	$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 9m $\Omega$	$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 13.5m $\Omega$
$V_{DS}$	60V								
$I_D$ (at $V_{GS}=10V$ )	13A								
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$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 13.5m $\Omega$								

SOP-8



Part Number	Package Type	Form	Marking
TSJ12N06AT	SOP-8	Tape & Reel	J12N06AT

**Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>B</sup>	$I_D$	$T_C = 25^\circ\text{C}$	13
		$T_C = 100^\circ\text{C}$	10.4
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	52	A
Avalanche Current <sup>A</sup>	$I_{AS}$	36	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ <sup>A</sup>	$E_{AS}$	65	mJ
Power Dissipation <sup>C</sup>	$P_D$	$T_C = 25^\circ\text{C}$	3.1
		$T_C = 100^\circ\text{C}$	2.1
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	$R_{\theta JC}$	24	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient			
	$R_{\theta JA}$	40	



Electrical Characteristics( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)							
Symbol	Parameter	Conditions	Value			Units	
			Min	Typ	Max		
<b>STATIC PARAMETERS</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60	--	--	V	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^{\circ}\text{C}$	--	--	1	$\mu\text{A}$
			$T_J = 125^{\circ}\text{C}$	--	--	100	
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	--	--	$\pm 100$	nA	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	--	2.5	V	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 12\text{A}$	--	6.5	9	$\text{m}\Omega$	
		$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$	--	10.7	13.5	$\text{m}\Omega$	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 12\text{A}$	--	85	--	S	
$V_{SD}$	Diode Forward Voltage	$I_S = 1\text{A}, V_{GS} = 0\text{V}$	--	--	1	V	
$I_S$	Maximum Body-Diode Continuous Current <sup>B</sup>		--	--	4	A	
<b>DYNAMIC PARAMETERS</b>							
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 30\text{V}, f = 1\text{MHz}$	--	2455	--	$\text{pF}$	
$C_{oss}$	Output Capacitance		--	240	--		
$C_{rss}$	Reverse Transfer Capacitance		--	34	--		
<b>SWITCHING PARAMETERS</b>							
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 12\text{A}$	--	45	--	nC	
$Q_g(4.5\text{V})$			--	24	--		
$Q_{gs}$			Gate Source Charge	--	6.8		--
$Q_{gd}$			Gate Drain Charge	--	11.5		--
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 12\text{A}, R_G = 3\Omega$	--	8	--	ns	
$t_r$	Turn-On Rise Time		--	3	--		
$T_{D(off)}$	Turn-Off Delay Time		--	25	--		
$t_f$	Turn-Off Fall Time		--	4	--		
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 12\text{A}, di/dt = 500\text{A}/\mu\text{s}$	--	15	--	ns	
$Q_{rr}$	Body Diode Reverse Recovery Charge		--	55	--	nC	

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation  $P_D$  is based on  $T_{J(MAX)} = 175^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

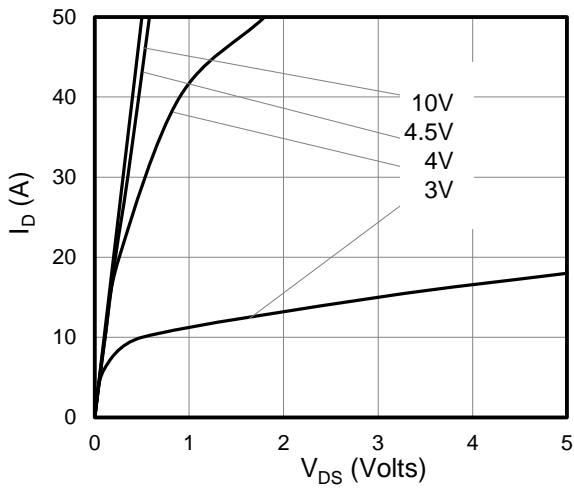


Figure 1: On-Region Characteristics

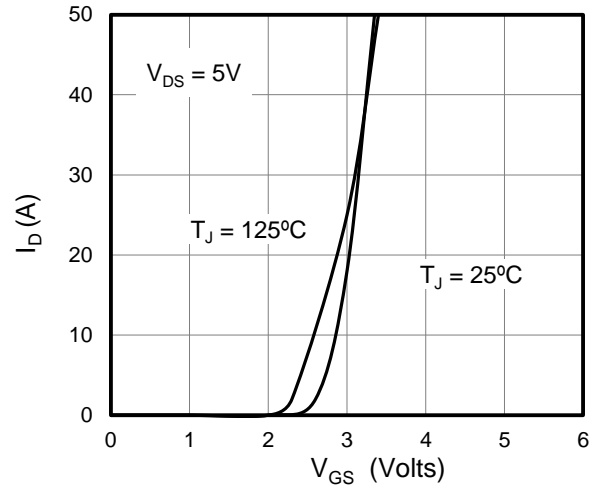


Figure 2: Transfer Characteristics

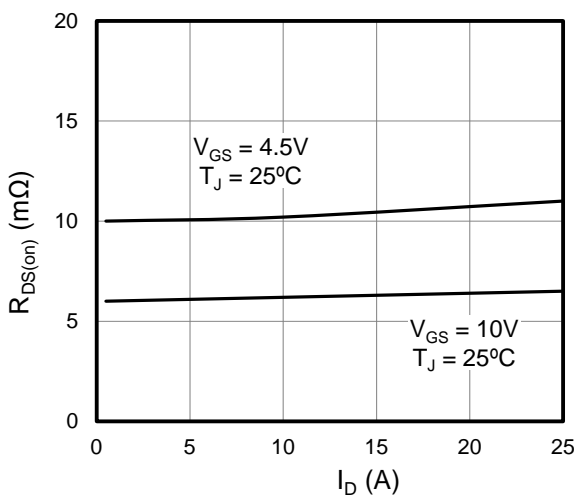


Figure 3: On-Resistance vs. Drain Current

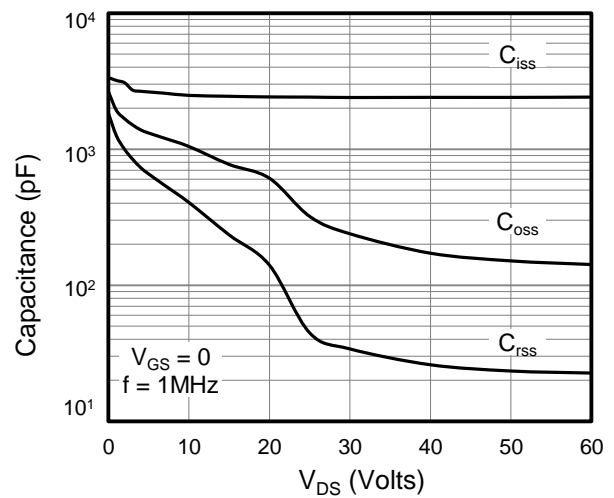


Figure 4: Capacitance Characteristics

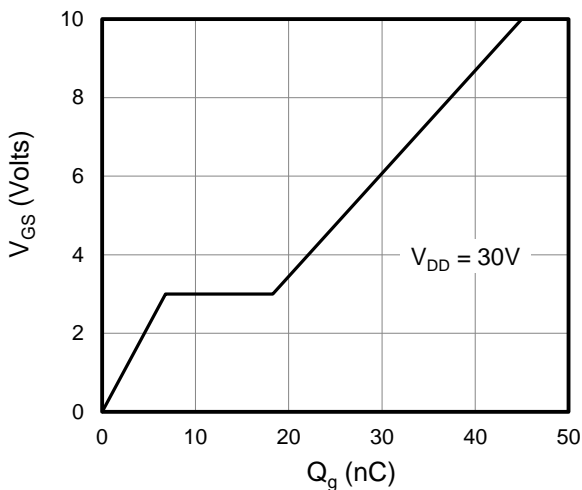


Figure 5: Gate Charge Characteristics

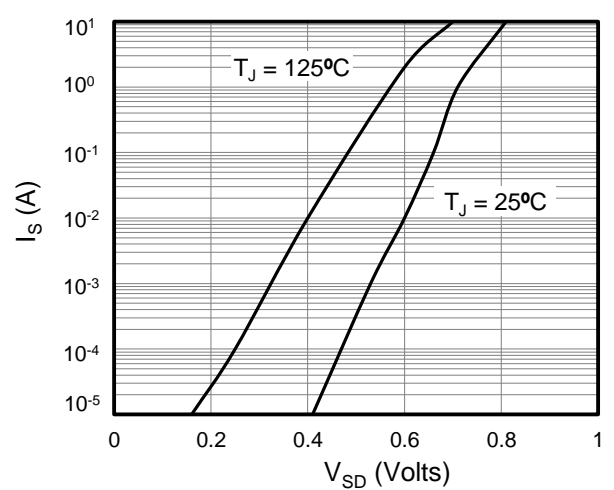


Figure 6: Body Diode Forward Voltage



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

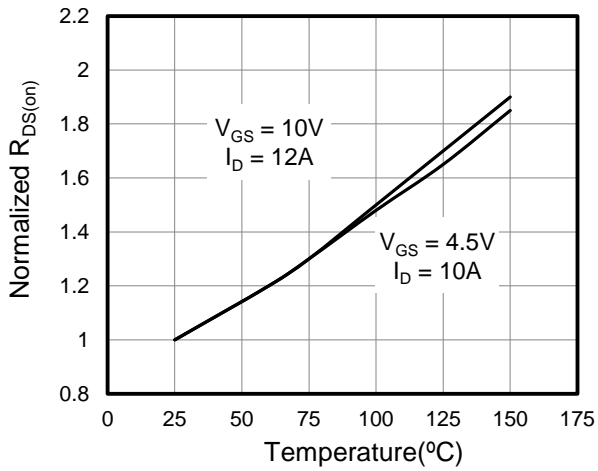


Figure 7: On-Resistance vs. Junction Temperature

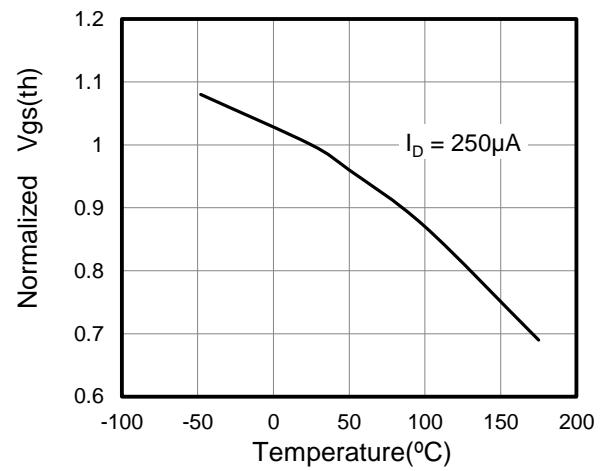


Figure 8:  $V_{GS(th)}$  vs. Junction Temperature

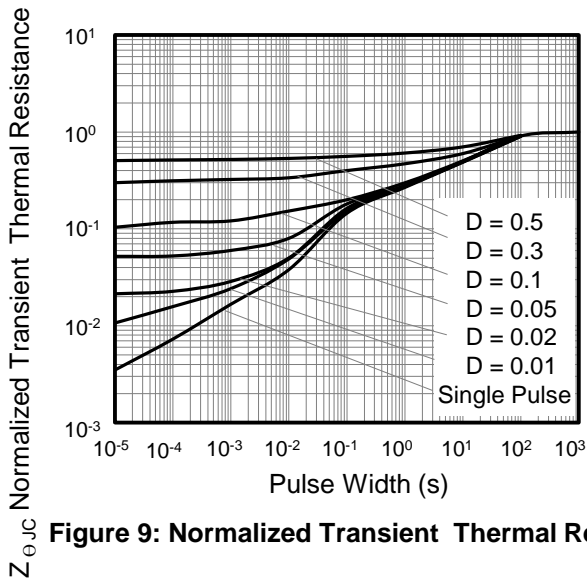


Figure 9: Normalized Transient Thermal Resistance

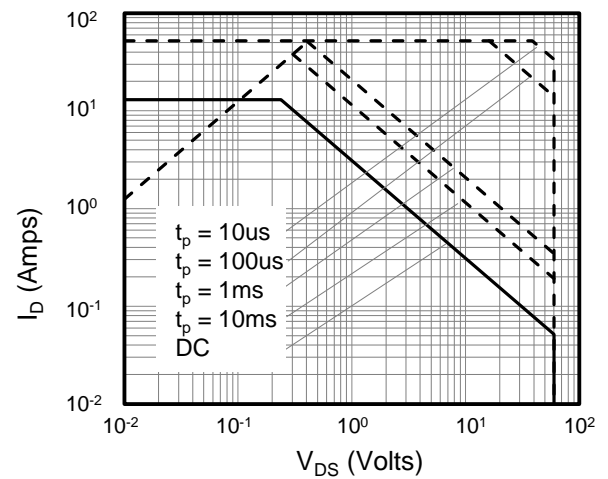


Figure 10: Safe Operating Area



Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

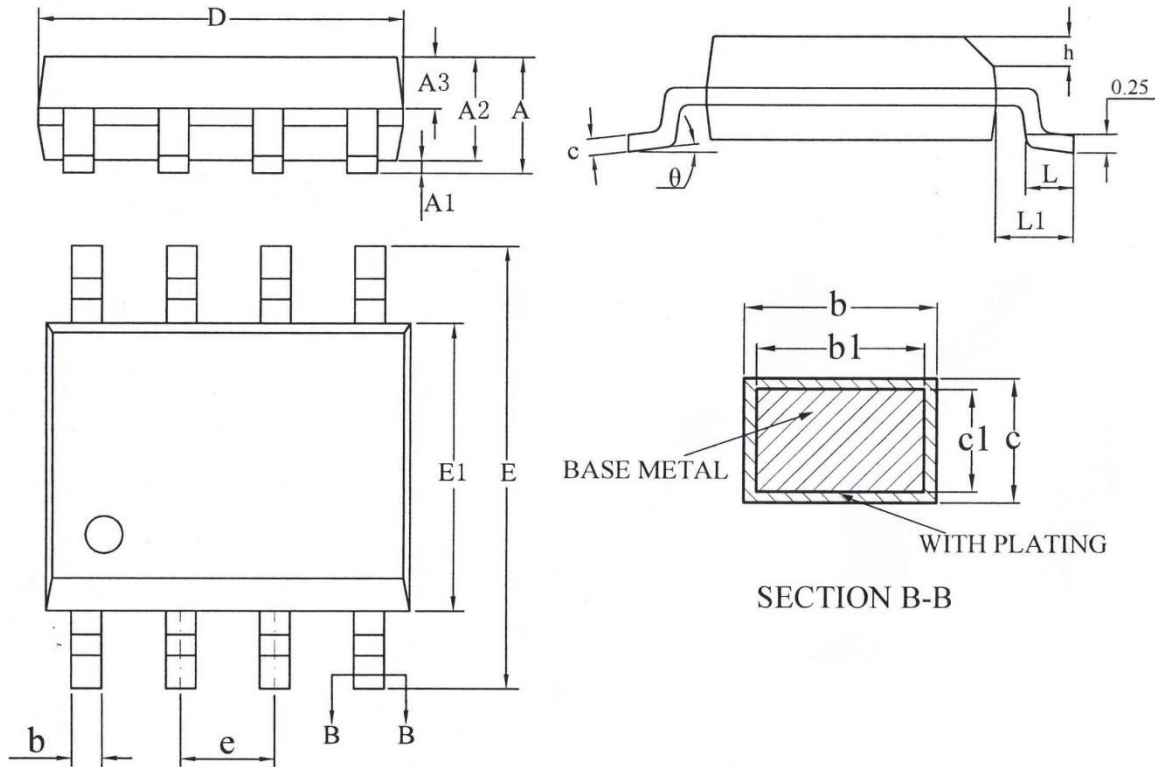


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





### SOP-8



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	1.75
A1	0.10	—	0.225
A2	1.30	1.40	1.50
A3	0.60	0.65	0.70
b	0.39	—	0.48
b1	0.38	0.41	0.43
c	0.21	—	0.26
c1	0.19	0.20	0.21

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	4.70	4.90	5.10
E	5.80	6.00	6.20
E1	3.70	3.90	4.10
e	1.27BSC		
h	0.25	—	0.50
L	0.50	—	0.80
L1	1.05BSC		
$\theta$	0	—	8°



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